

General Description

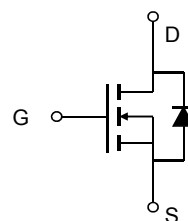
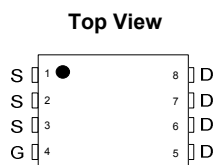
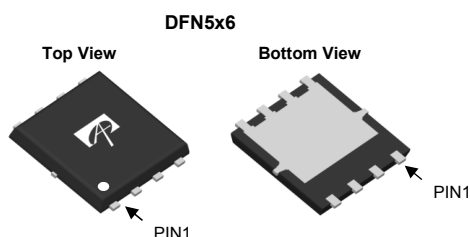
The AON6400 combines advanced trench MOSFET technology with a low resistance package to provide extremely low RDS(ON). This device is ideal for load switch and battery protection applications.

- RoHS and Halogen-Free Compliant.

Product Summary

V_{DS}	30V
I_D (at $V_{GS}=10V$)	85A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 1.4m Ω
$R_{DS(ON)}$ (at $V_{GS} = 4.5V$)	< 1.8m Ω

100% UIS Tested
100% R_g Tested



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ^G	$T_C=25^\circ\text{C}$	85	A
	$T_C=100^\circ\text{C}$	67	
Pulsed Drain Current ^C	I_{DM}	400	
Continuous Drain Current	$T_A=25^\circ\text{C}$	31	A
	$T_A=70^\circ\text{C}$	25	
Avalanche Current ^C	I_{AS}, I_{AR}	90	A
Avalanche energy $L=0.1\text{mH}$ ^C	E_{AS}, E_{AR}	405	mJ
Power Dissipation ^B	$T_C=25^\circ\text{C}$	200	W
	$T_C=100^\circ\text{C}$	83	
Power Dissipation ^A	$T_A=25^\circ\text{C}$	2.3	W
	$T_A=70^\circ\text{C}$	1.45	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	14	17	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^{A D}		40	55	$^\circ\text{C/W}$
Maximum Junction-to-Case	$R_{\theta JC}$	0.45	0.6	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±20V			1	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	1.2	1.7	2.2	V
I _{D(ON)}	On state drain current	V _{GS} =10V, V _{DS} =5V	400			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A T _J =125°C		1.15	1.4	mΩ
				1.75	2.1	
		V _{GS} =4.5V, I _D =20A		1.45	1.8	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A		140		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.65	1	V
I _S	Maximum Body-Diode Continuous Current				85	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz	5500	6900	8300	pF
C _{oss}	Output Capacitance		740	1060	1380	pF
C _{rss}	Reverse Transfer Capacitance		440	730	1020	pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.6	1.2	1.8	Ω
SWITCHING PARAMETERS						
Q _g (10V)	Total Gate Charge	V _{GS} =10V, V _{DS} =15V, I _D =20A	110	140	170	nC
Q _g (4.5V)	Total Gate Charge		55	70	84	nC
Q _{gs}	Gate Source Charge		16	20	24	nC
Q _{gd}	Gate Drain Charge		20	32	45	nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =0.75Ω, R _{GEN} =3Ω		12		ns
t _r	Turn-On Rise Time			13		ns
t _{D(off)}	Turn-Off DelayTime			88		ns
t _f	Turn-Off Fall Time			32		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =20A, dI/dt=500A/μs	15	19	23	ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =20A, dI/dt=500A/μs	44	55	66	nC

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The Power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 150° C may be used if the PCB allows it.

B. The power dissipation P_D is based on T_{J(MAX)}=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150° C. Ratings are based on low frequency and duty cycles to keep initial T_J=25° C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is limited by package.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

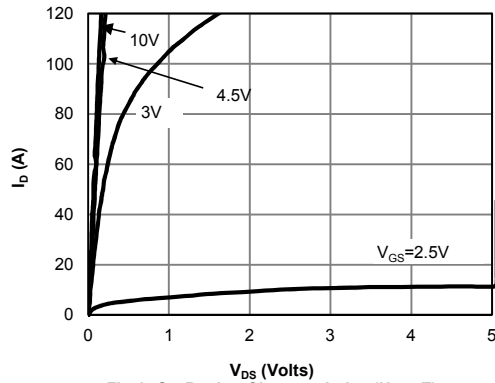


Fig 1: On-Region Characteristics (Note E)

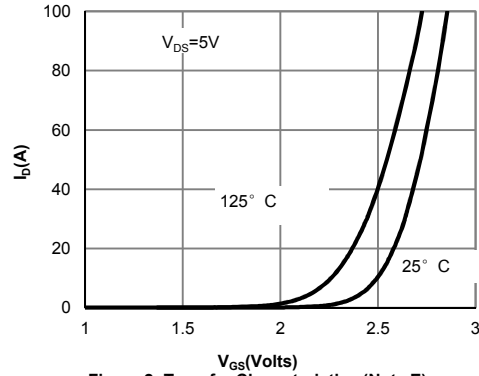


Figure 2: Transfer Characteristics (Note E)

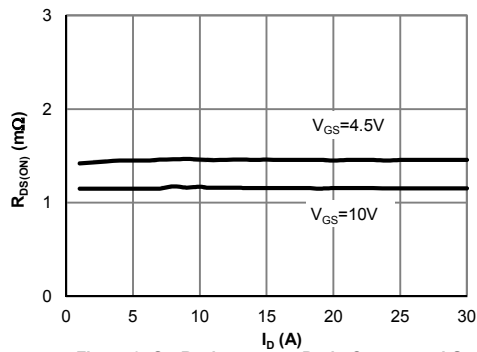


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

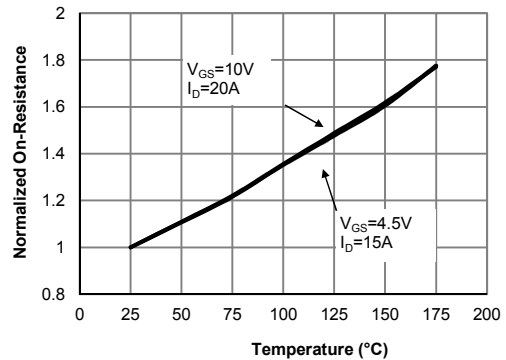


Figure 4: On-Resistance vs. Junction Temperature (Note E)

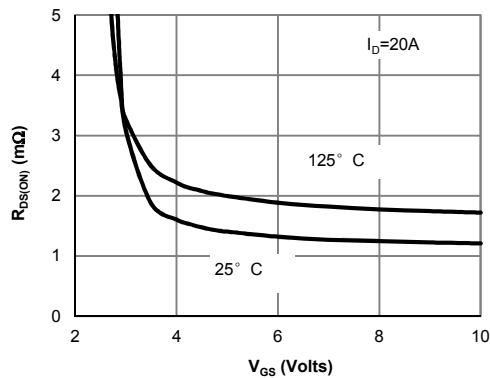


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

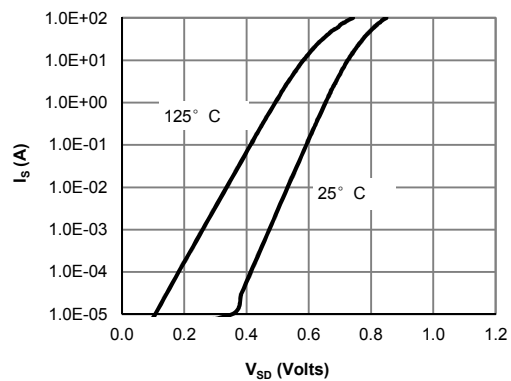
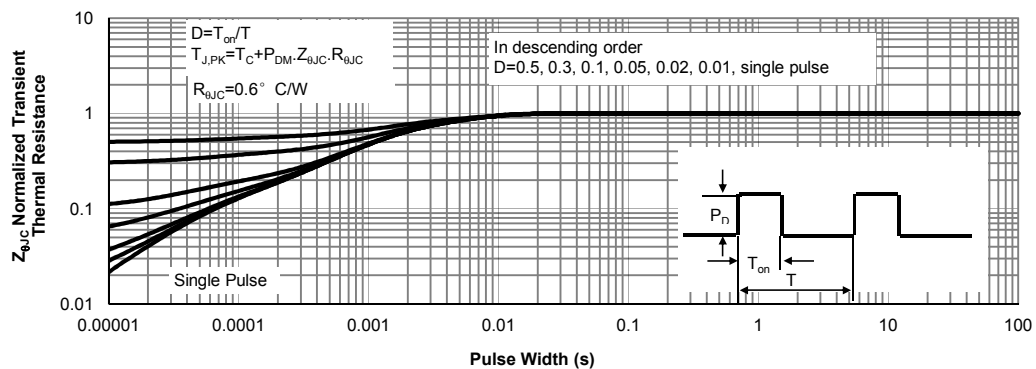
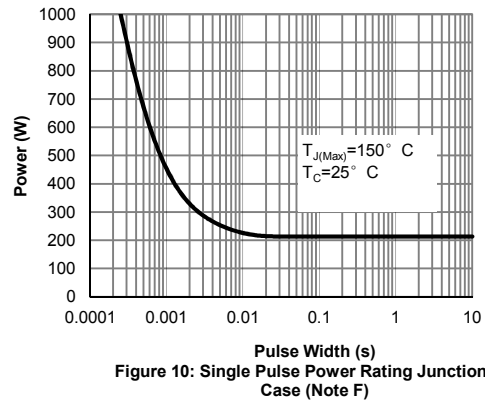
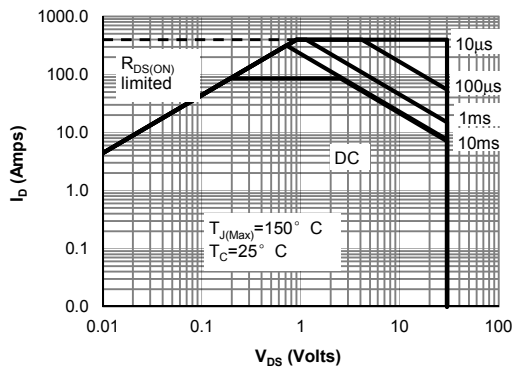
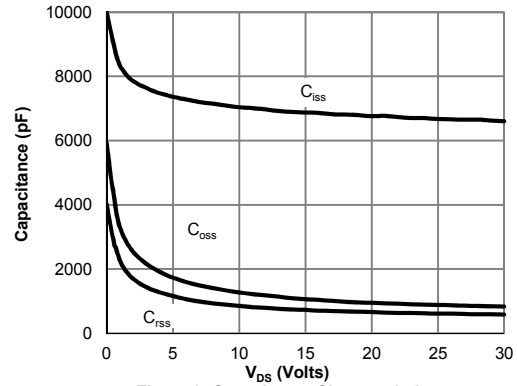
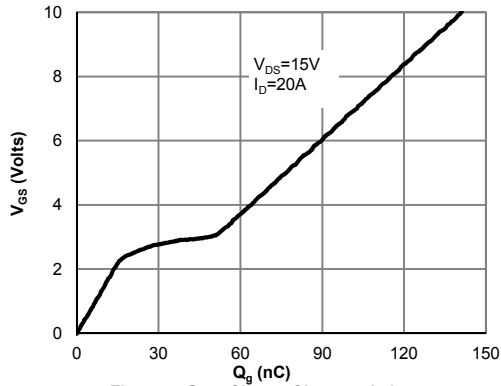
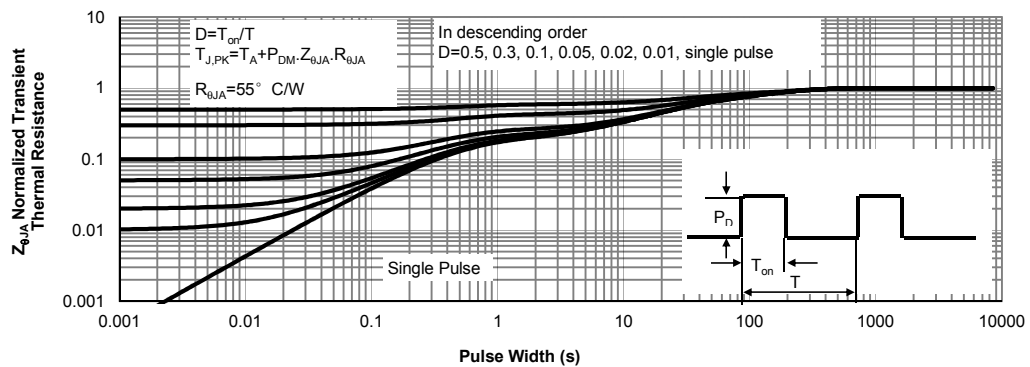
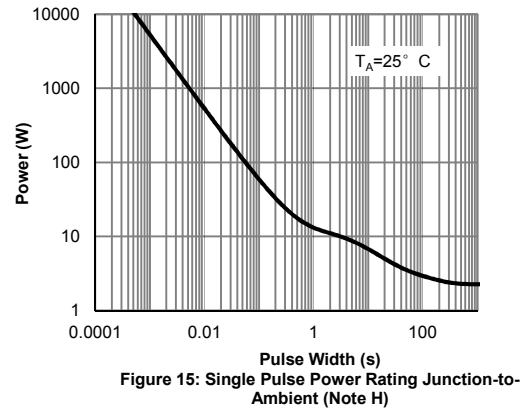
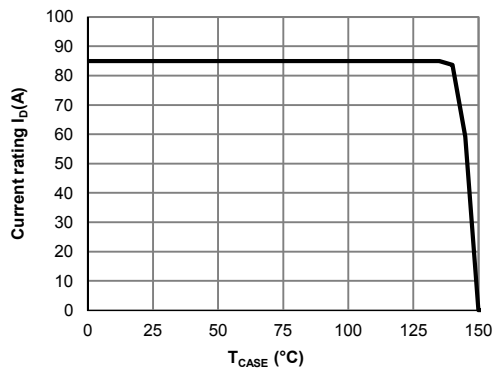
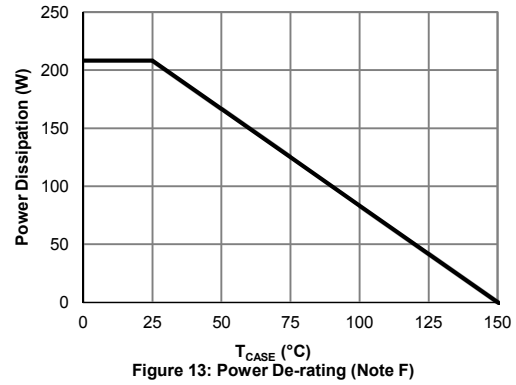
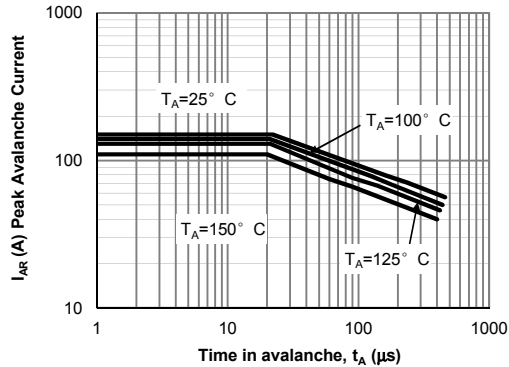


Figure 6: Body-Diode Characteristics (Note E)

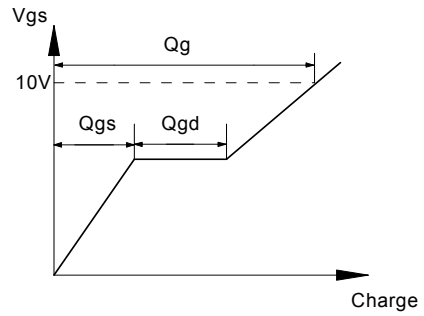
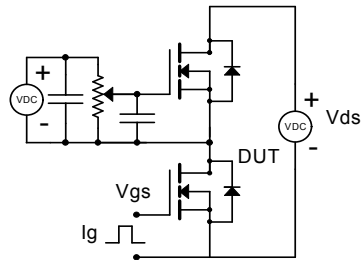
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



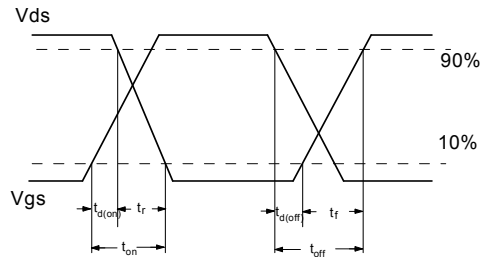
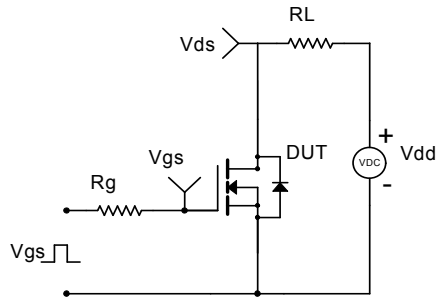
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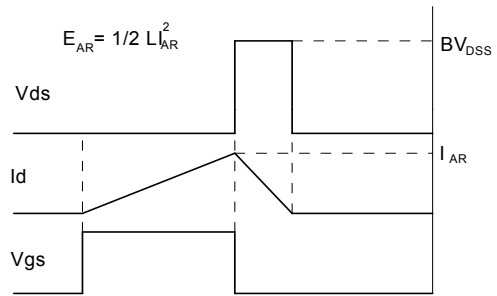
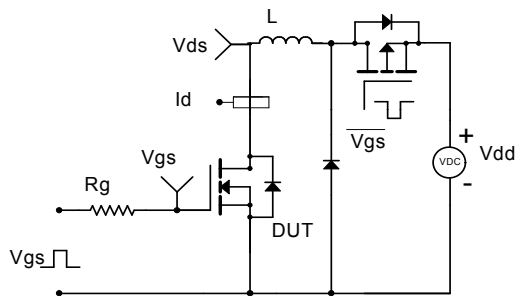
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

